High Power Laser Diode TO-Cans



Part Number: TO9-266

High Power Triple Junction TO9 Package Multi-Mode Fabry-Perot Pulsed Wavelength at 1550nm Lensed Options Available

Features

- High Output Power
- High Dynamic Range
- High Efficiency
- Standard TO9
- Cost Effective

Application

- Professional Medical
- Home Use Medical
- Laser Range Finder
- Target Illumination
- Military Systems
- TOF LiDAR for Automotive and Drones
- Telecom OTDR
- Optical Comm



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.





Specification

TO9-266



Optical	Symbol	Тур.	Units
Center Wavelength	λ _c	1550	nm (±20)
Output Power (<10ns)*	Pout	60	Watts (±10%)
Output Power (150ns)*	Pout	52	Watts (±10%)
Emitter Width	W	180	μm
Spectral Width FWHM	Δλ	22	nm
Slope Efficiency	η	0.9	W/A
Fast Axis Div.	Θ⊥	28	deg FWHM
Slow Axis Div.	Θ _{II}	12	deg FWHM
Electrical	Symbol		Units
Power Conversion Eff.	η	9	%
Operating Current (<10ns)	lop	60	A
Operating Current (150ns)	l _{op}	56	А
Threshold Current	Ітн	2	А
Operating Voltage	V _{op}	10	V
Duty Cycle	DC	0.1	%
Mechanical	Symbol	Range	Units
Operating Temp.**		-40 to 60	°C
Storage Temp.		-40 to 80	°C

*Specified values are rated at a constant heat sink temperature of 20°C. **High temperature operation will reduce performance and MTTF. Unless otherwise indicated all values are nominal.

*Available Lenses & Caps

Part Number	Description	
TO9-266	TO9 Uncapped	
TO9-266-181	TO9 5.8mm Tall Cap, FAC Lens Collimated<5mrad f=1.2mm,5mm lg	
TO9-266-140	TO9 5.8mm Tall Cap, Lens Matched f=171um, 5.0 lg	
TO9-266-161	TO9 Cap 5.8mm Tall	

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SemiNex Laser Diodes TO9-266

Graphs & Data

60 LIV Plot

50

40

30

20

10

0

Optical Power (W)

Typical TO9 L-I-V Characteristics

Voltage (V)

20

15

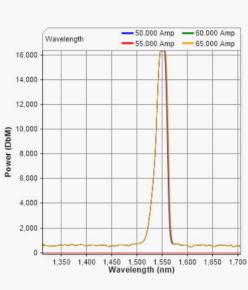
Voltage (V)

5

Optical Power (W)

Typical TO9 Output Spectrum

*Tested with 150nsec pulse @ 0.1% Duty Cycle



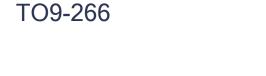




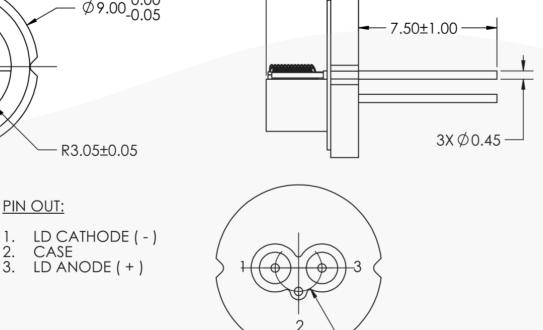
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3.50±0.25 Ø8.10±0.30 Ø9.00_0.00

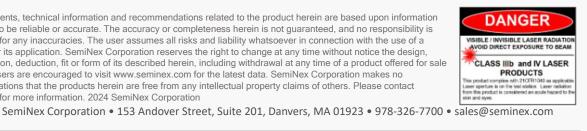
1. 2.3.



Mechanical Drawing



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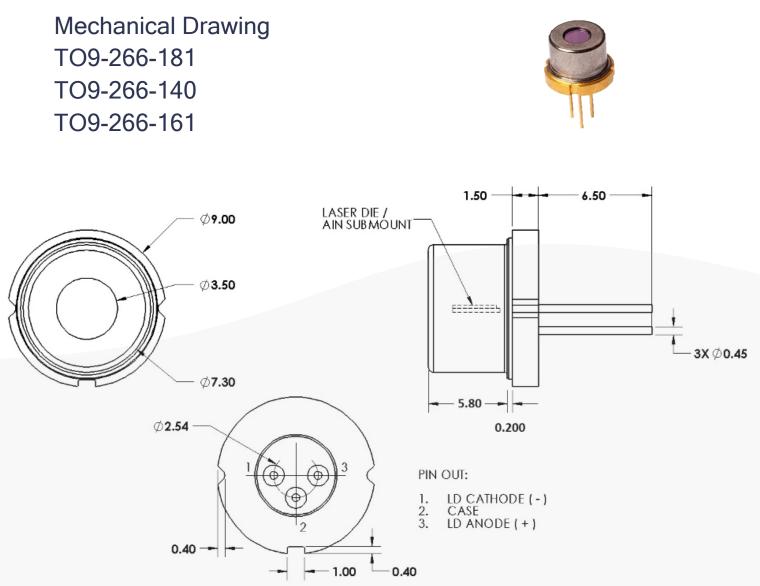


Ø2.54





1.50±0.05



High Power Laser Diode

TO-Cans

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